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ABSTRACT OF THE DISCLOSURE

[0039] An anti-fuse structure and a method for forming the anti-fuse structure employ a substrate having formed therein a contact region. A metal silicide layer is formed over and electrically connected with the contact region. A first doped polysilicon layer is formed upon the metal silicide layer. An anti-fuse material layer is formed upon the first doped polysilicon layer. A second doped polysilicon layer is formed upon the anti-fuse material layer. The first doped polysilicon layer and the second doped polysilicon layer may be formed with the same or complementary dopant polarity, the latter providing an anti-fuse diode.